

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	(double near gate near transistor and back near gate near dielectric and front near gate near electrode and vertical near spacer an oxidizing near3 back near gate). clm.	US-PGPUB; USPAT	OR	OFF	2006/12/11 06:59
L2	15372	double near gate near transistor and back near gate near dielectric and front near gate near electrode and vertical near spacer an oxidizing near3 back near gate	US-PGPUB; USPAT	OR	OFF	2006/12/11 06:59
L3	1	double near gate near transistor and back near gate near dielectric and front near gate near electrode and vertical near spacer and oxidizing near3 back near gate	US-PGPUB; USPAT	OR	OFF	2006/12/11 07:00
L4	443	double near gate near transistor	US-PGPUB; USPAT	OR	OFF	2006/12/11 07:00
L5	435	4 and source and drain	US-PGPUB; USPAT	OR	OFF	2006/12/11 07:00
L6	17	5 and back near gate and front near gate	US-PGPUB; USPAT	OR	OFF	2006/12/11 07:00